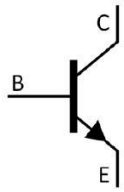
TO-126 NPN Silicon NPN transistor in a TO-126 Plastic Package.

$V_{CEO}$

High $V_{CEO}$ Large DC current, high $f_T$, low $V_{CE(sat)}$.

Low power audio amplifier, high speed switching applications.



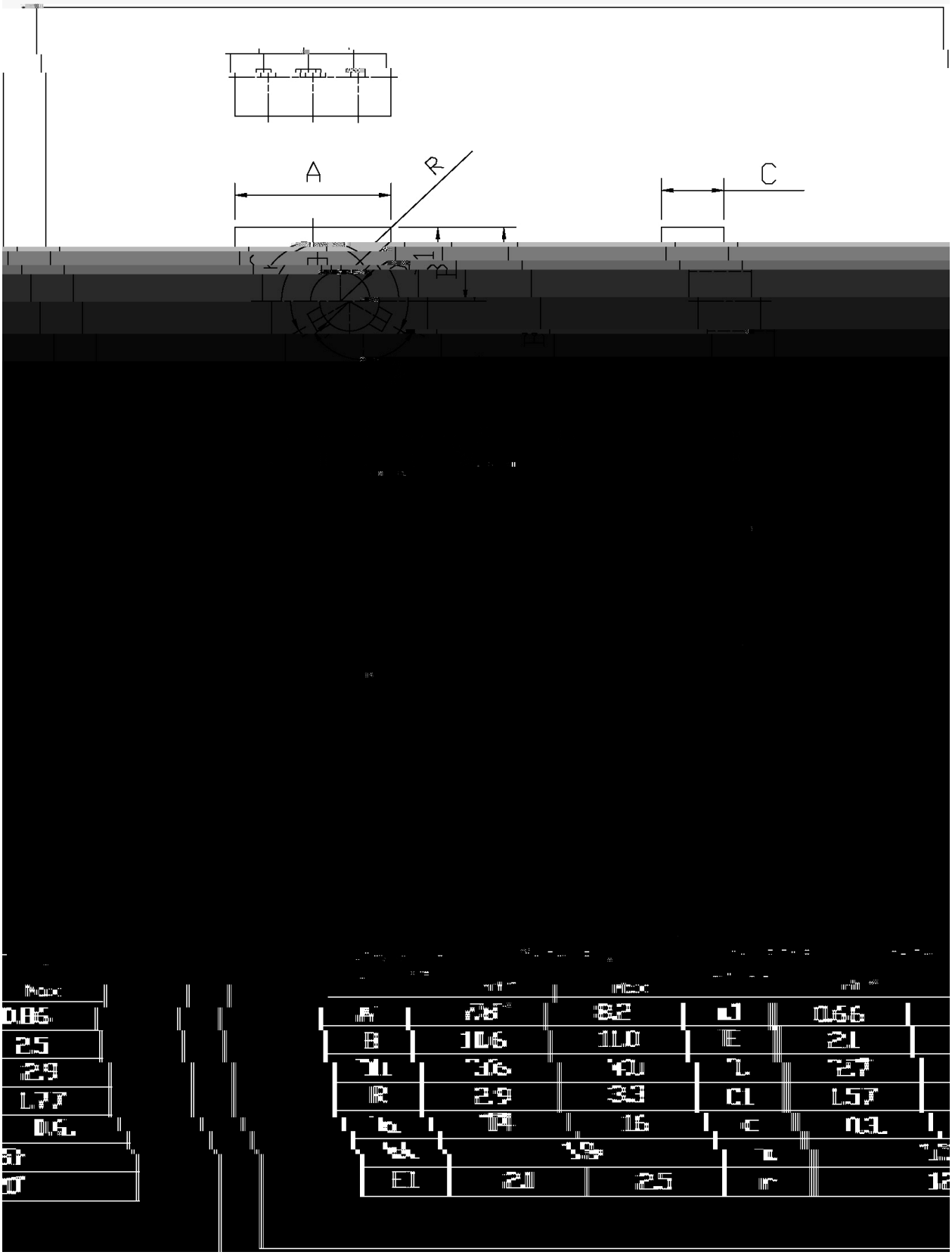



PIN1 Emitter PIN 2

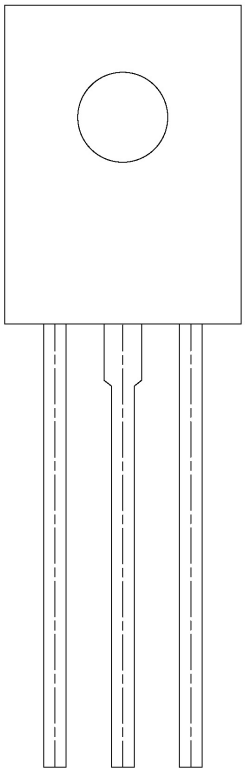
| Parameter | Symbol | Rating | Unit |
|---|---|---|---|
| Collector to Base Voltage | $V_{CBO}$ | 100 | V |
| Collector to Emitter Voltage | $V_{CEO}$ | 100 | V |
| Emitter to Base Voltage | $V_{EBO}$ | 7.0 | V |

## / Electrical Characteristic Curve

## / Package Dimensions



## / Marking Instructions



BR

MJE243

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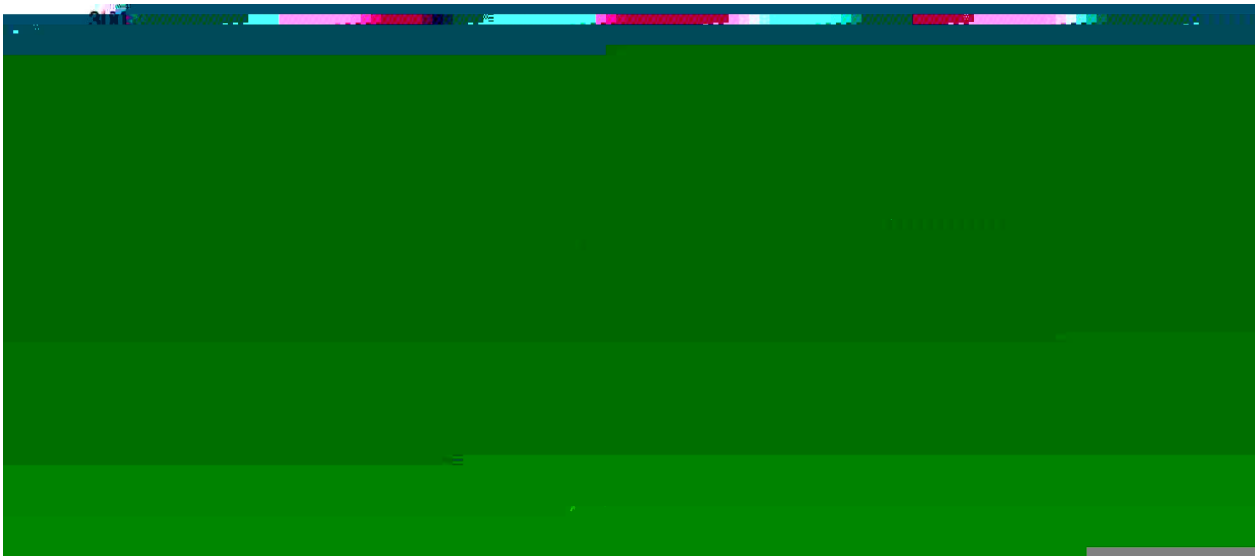
Note:

BR:

## ( ) / Temperature Profile for Dip Soldering(Pb-Free)



| | | | |
|---|---|---|---|
| | | | Note: |
| 1 | 25 150 | 60 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | 5±0.5sec; | 2.Peak Temp.:255±5 , Duration:5±0.5sec. |
| 3 | | 2 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

## / Resistance to Soldering Heat Test Conditions

| | | | |
|---|---|---|---|
| 270±5 | 10±1 sec. | Temp.:270±5 | Time:10±1 sec |

## / Packaging SPEC.

/ BULK

| Package Type | Units | | | | | Dimension (unit mm$^3$) | | | |
|---|---|---|---|---|---|---|---|---|---|
| | Units/Tube / | Tubes/Inner Box / | Units/Inner Box / | Inner Boxes/Outer Box / | Units/Outer Box / | Tube | Inner Box | Outer Box | 3Ŧj7i55 |